



DMP32D4S

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> Max	I <sub>D</sub> Max @T <sub>A</sub> = +25°C
-30V	2.4Ω @ V <sub>GS</sub> = -10V	-300mA
-30 V	4Ω @ V <sub>GS</sub> = -4.5V	-250mA

### Description

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### Applications

- Load Switch
- Portable Applications
- Power Management Functions

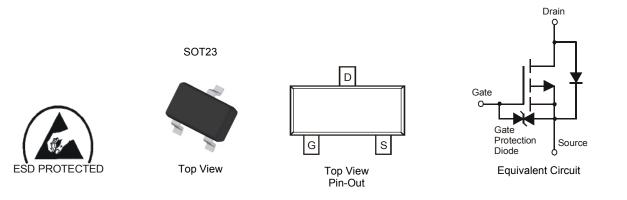
### **30V P-CHANNEL ENHANCEMENT MODE MOSFET**

### Features

- Low On-Resistance
- ESD Protected Gate to 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe). (3)
- Weight: 0.006 grams (approximate)



### Ordering Information (Note 4)

Part Number	Case	Packaging
DMP32D4S-7	SOT23	3,000/Tape & Reel
DMP32D4S-13	SOT23	10,000/Tape & Reel

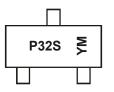
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



P32S = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Z = 2012) M = Month (ex: 9 = September)

Date Code Key

Year	2012	2	2013		2014	20	15	2016		2017		2018
	2012	-	2010		2017	20	10	2010		2017	4	-010
Code	Z		A		В		2	D		E		F
						•			· · · ·			
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Character	istic		Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6)	V <sub>GS</sub> = -10V	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	300 250	mA
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-1	А

### Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units	
Tatal Dowar Dissinction	(Note 5)	D	370	mW	
Total Power Dissipation	(Note 6)	PD	540	IIIVV	
Thermal Resistance, Junction to Ambient	(Note 5)		348		
Thermal Resistance, surretion to Ambient	(Note 6)	R <sub>0JA</sub>	241	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R <sub>θJC</sub>	91		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	Symbol	WIIII	тур	INIAA	Unit	Test condition
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30		_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -1mA
Zero Gate Voltage Drain Current TJ = +25°C	IDSS	_	_	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 16V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)	000			1		
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.4 -1.2		-2.4 -2.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$ $V_{DS} = -5V, I_D = -1 \mu A$
Static Drain-Source On-Resistance	Б			2.4	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -0.3A
	R <sub>DS (ON)</sub>	_	_	4	12	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -0.25A
Forward Transfer Admittance	Y <sub>fs</sub>	—	6	_	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -400mA
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -300mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>	_	51.16	—	pF	
Output Capacitance	C <sub>oss</sub>		10.85	—	рF	−V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, −f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	8.88		pF	1 - 1:00012
Gate Resistance	Rg	—	275	_	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Qq		0.6	—	nC	V <sub>GS</sub> = -4.5V
Total Gate Charge	Qg	—	1.2	_	nC	V <sub>DS</sub> = -10V,
Gate-Source Charge	Q <sub>gs</sub>		0.2	—	nC	V <sub>GS</sub> = -10V I <sub>D</sub> = -1A
Gate-Drain Charge	Q <sub>qd</sub>	_	0.3	—	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	_	9.86		ns	
Turn-On Rise Time	tr	_	11.5	—	ns	V <sub>DS</sub> = -15V, I <sub>D</sub> = -1A
Turn-Off Delay Time	t <sub>D(off)</sub>		31.8	—	ns	$V_{GS} = -10V, R_{G} = 6\Omega$
Turn-Off Fall Time	t <sub>f</sub>		21.9		ns	7

Notes:

Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.



T<sub>A</sub> = 150°C

vs. Gate-Source Voltage

25

0

50

75

100

125

T<sub>A</sub> = 125°C

85

5

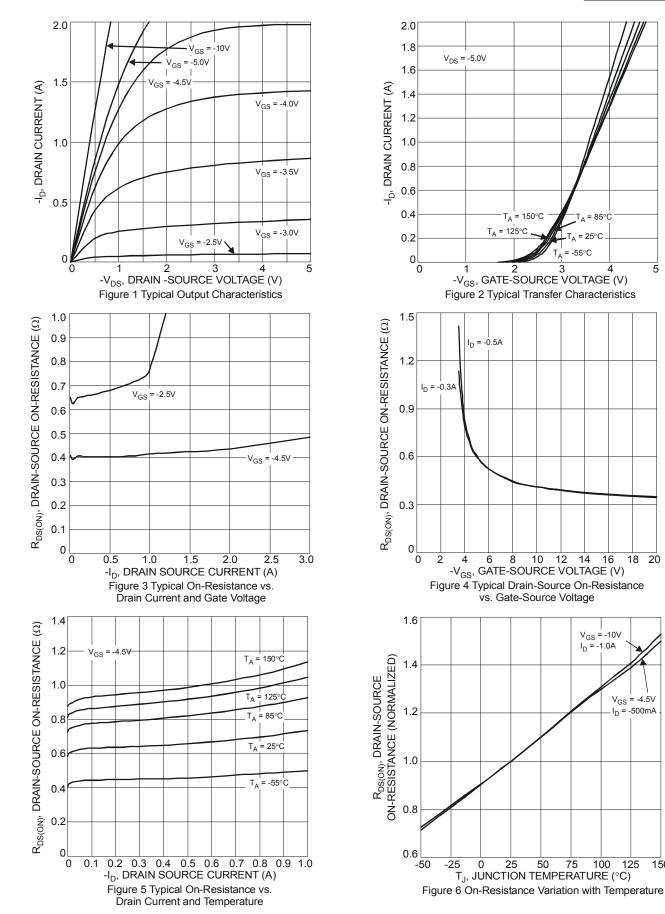
18 20

V<sub>GS</sub> = -4.5V I<sub>D</sub> = -500mA

V<sub>GS</sub> = -10V I<sub>D</sub> = -1.0A

25°C

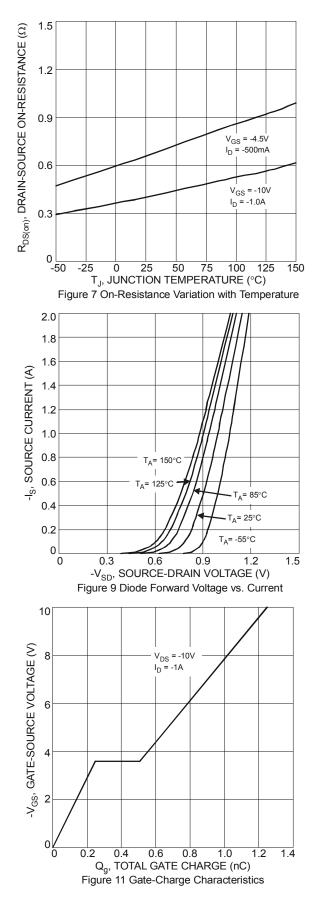
= -55°C

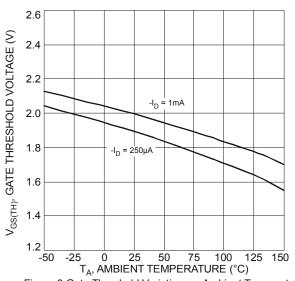


150

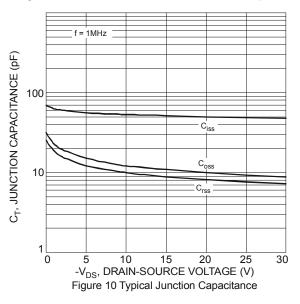








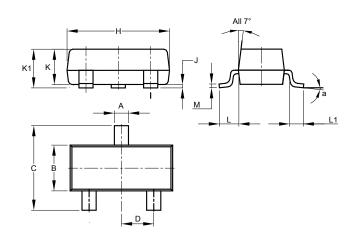






# **Package Outline Dimensions**

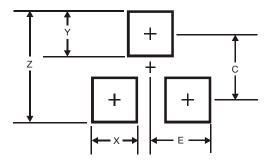
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
в	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
H	2.80	3.00	2.90					
J	0.013	0.10	0.05					
К	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	8°							
All	All Dimensions in mm							

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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